



TO-92 Plastic-Encapsulate Transistors

2SA673A TRANSISTOR (PNP)

FEATURE

Power dissipation

$$P_{CM} : 0.4 \text{ W (Tamb=25}^{\circ}\text{C)}$$

Collector current

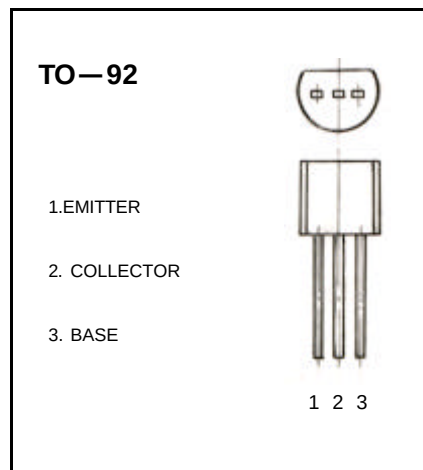
$$I_{CM} : -0.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -50 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55^{\circ}\text{C to } +150^{\circ}\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10 \mu\text{A}$, $I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1 \text{ mA}$, $I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu\text{A}$, $I_C = 0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20 \text{ V}$, $I_E = 0$			-0.5	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE} = -3 \text{ V}$, $I_C = -10 \text{ mA}$	60		320	
	$h_{FE(2)}$	$V_{CE} = -3 \text{ V}$, $I_C = -500 \text{ mA}$	10			
Collector-emitter saturation voltage	V_{CEsat}^*	$I_C = -150 \text{ mA}$, $I_B = -15 \text{ mA}$			-0.6	V
Base-emitter voltage	V_{BE}	$V_{CE} = -3 \text{ V}$, $I_C = -10 \text{ mA}$			-0.75	V

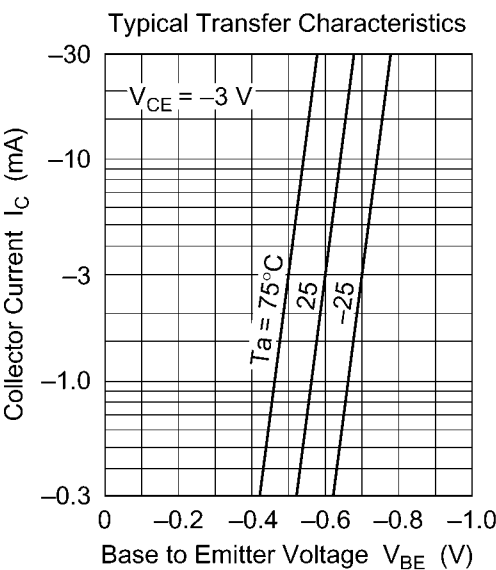
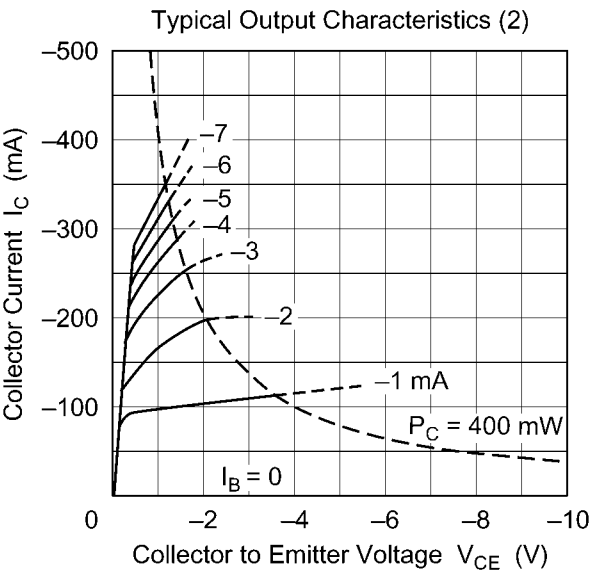
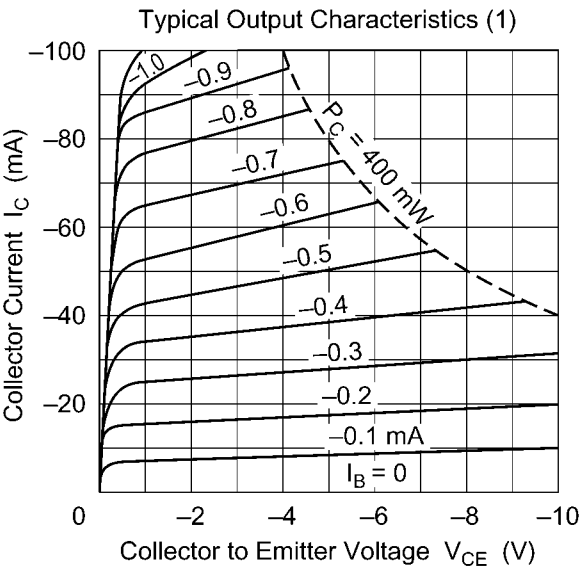
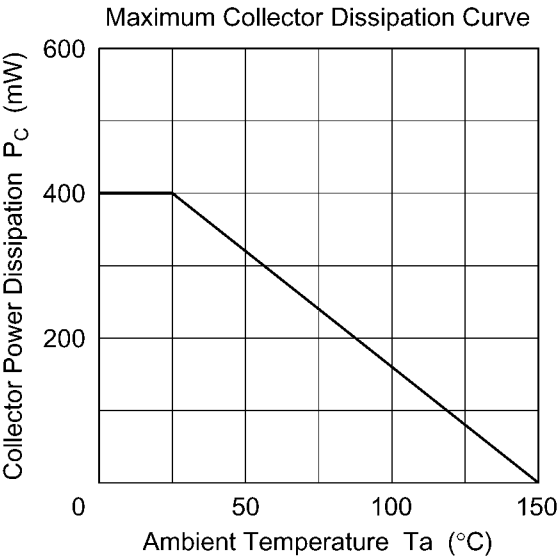
*Measured using pulse

CLASSIFICATION OF $h_{FE(1)}$

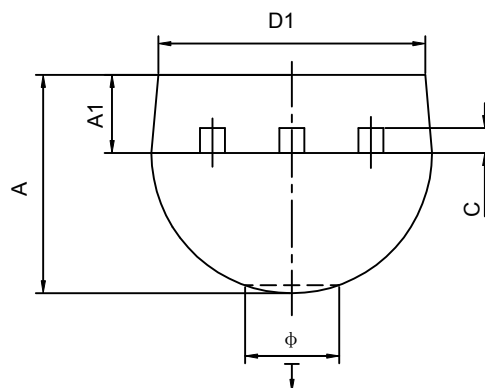
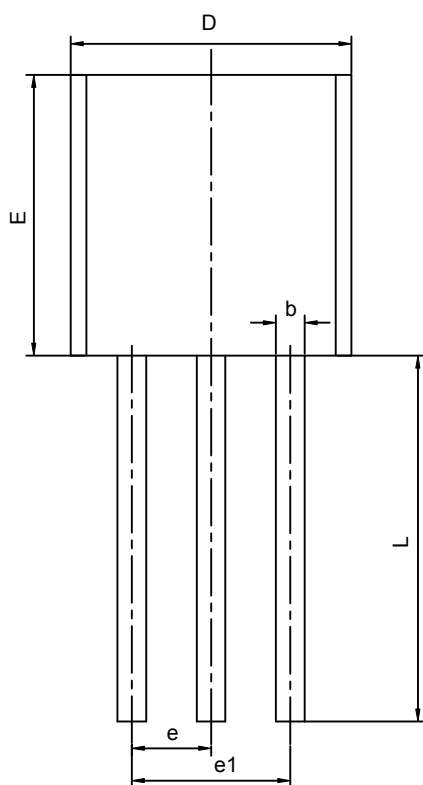
Rank	B	C	D
Range	60-120	100-200	160-320

Typical characteristics

2SA673A



TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
$\downarrow$	0.000	0.380	0.000	0.015